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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Masaki KURASAWA et al.**

Group Art Unit: 2814

Serial No.: 09/960,398

Examiner: **Thao Le**

Filed: **September 24, 2001**

P.T.O. Confirmation No.: 5650

For: **CAPACITOR AND METHOD FOR FABRICATING THE SAME, AND
SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME**

AMENDMENT UNDER 37 C.F.R. §1.111

Commissioner for Patents
Washington, D.C. 20231
Sir:

December 16, 2002

In response to the Office Action dated August 14, 2002, extended to December 14, 2002 by a one month Petition for Extension of Time, please amend the above-identified application as follows:

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IN THE CLAIMS:

Please amend claims 1, 3, 13 and 14 as follows:

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1. (Amended) A capacitor comprising:
 - a buffer structure formed on a substrate, the buffer structure having a height larger than a width thereof;
 - a lower electrode formed on the buffer structure;
 - a capacitor dielectric film formed on the lower electrode, and formed of a perovskite ferroelectric material having a smaller thermal expansion coefficient than that of the buffer structure and having a crystal oriented substantially perpendicular to a surface of the lower electrode; and
 - an upper electrode formed on the capacitor dielectric film.